

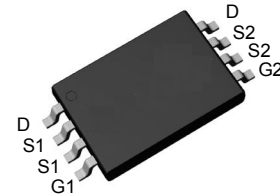
Features

- 20V/12A,
 $R_{DS(ON)} = 12.5m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
 $R_{DS(ON)} = 16m\Omega(\text{typ.}) @ V_{GS} = 2.5V$
- 100% UIS Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- ESD protection

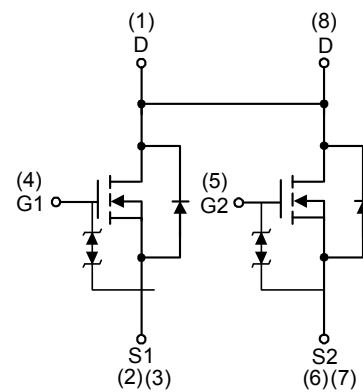
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Pin Description



Top View of TSSOP8



N-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		± 12	
I_D	Continue Drain Current	$T_A = 25^\circ\text{C}$	12	A
		$T_A = 70^\circ\text{C}$	4.8	
I_{DM}	Pulsed Drain Current	$T_A = 25^\circ\text{C}$	36	
I_S	Diode continuous forward current		12	A
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	
P_D	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	1.25	W
		$T_A = 70^\circ\text{C}$	0.8	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		100	$^\circ\text{C/W}$

Note * : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

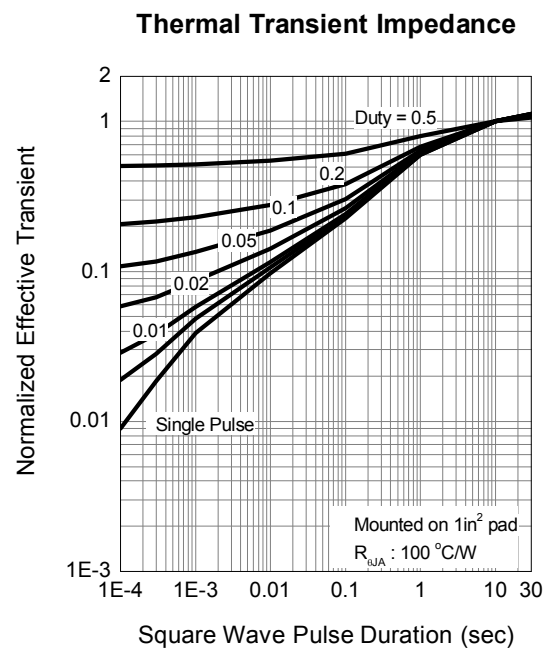
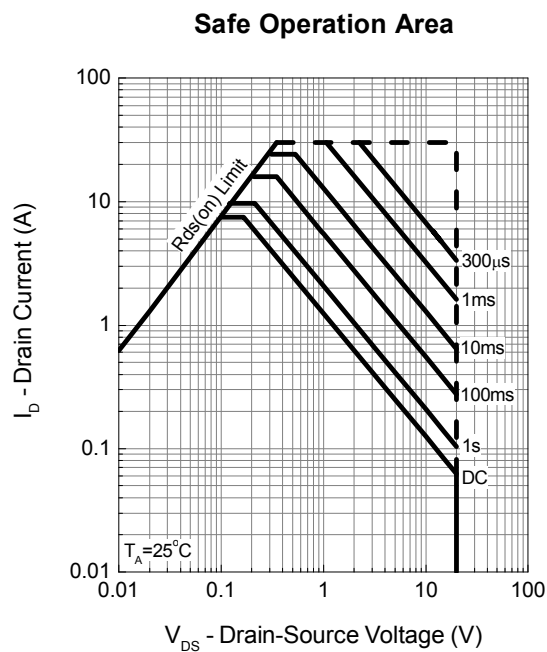
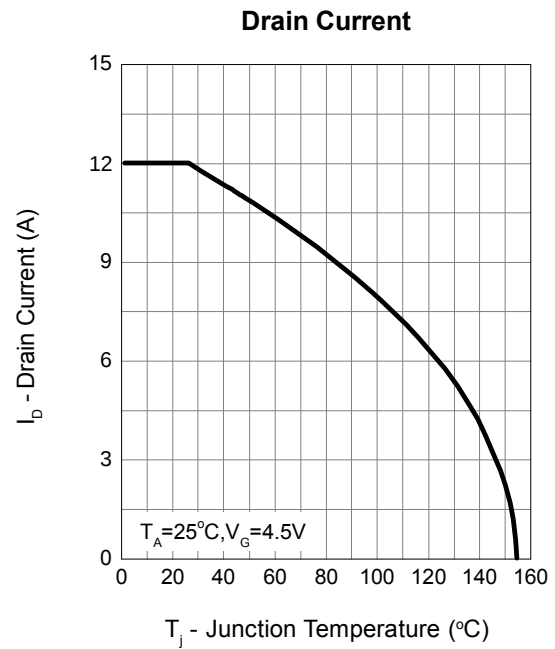
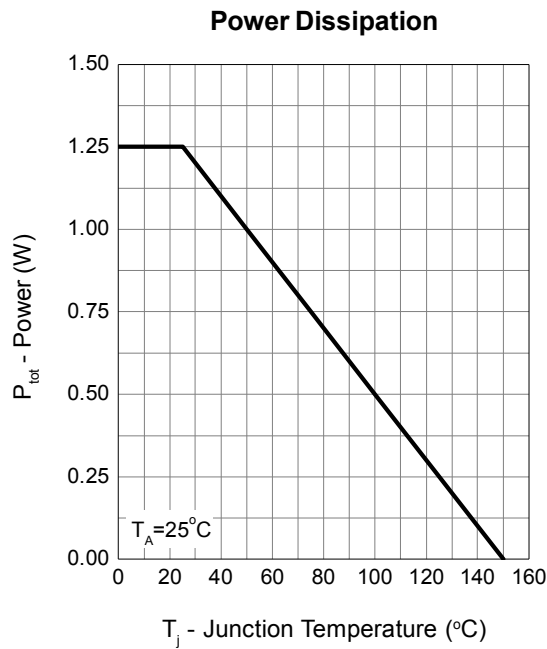
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	0.7	1.1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V	-	-	±10	uA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =4A V _{GS} =2.5V, I _{DS} =3A	- -	12.5 16	14.5 19	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.7	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =7.5A, dI _{SD} /dt=100A/μs	-	10	-	nS
Q _{rr}	Reverse Recovery Charge		-	3.5	-	nC
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	8	-	Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz	-	713	-	pF
C _{oSS}	Output Capacitance		-	118	-	
C _{rSS}	Reverse Transfer Capacitance		-	96	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω	-	9	16	ns
t _r	Turn-on Rise Time		-	13	23	
t _{d(OFF)}	Turn-off Delay Time		-	55	99	
t _f	Turn-off Fall Time		-	36	65	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =7.5A	-	9.8	12.8	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	
Q _{gd}	Gate-Drain Charge		-	3.6	-	

Note a Pulse test ; pulse width≤300μs, duty cycle≤2%.

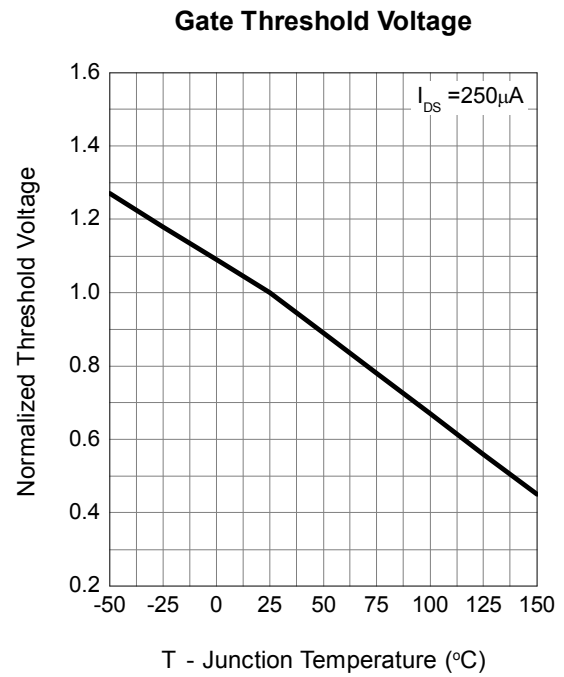
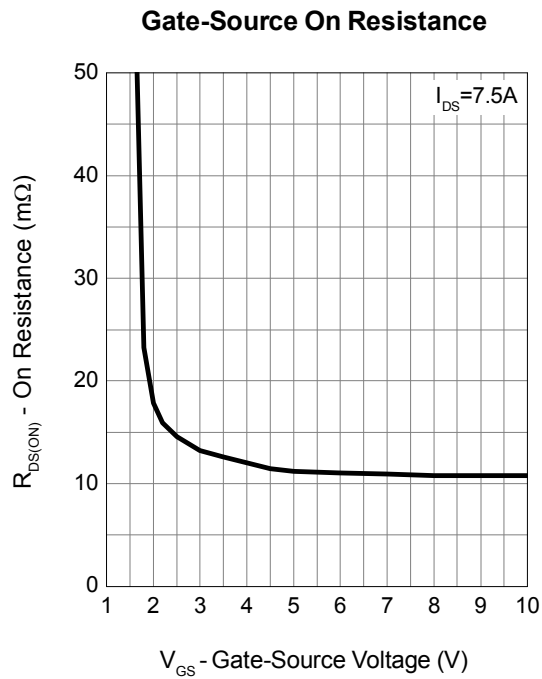
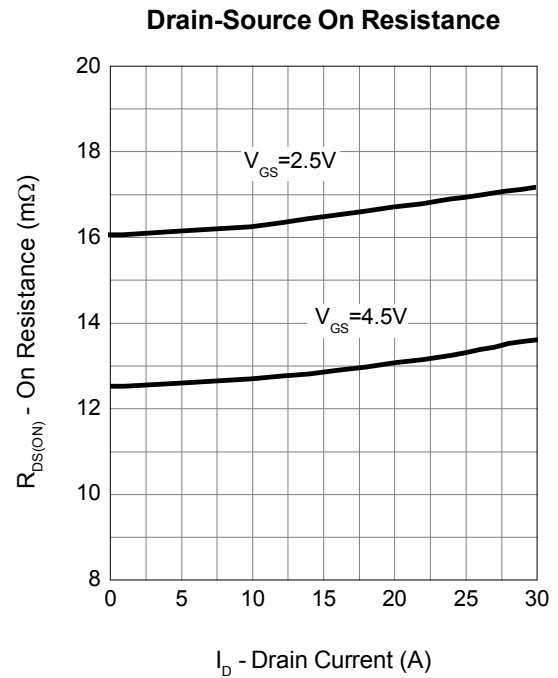
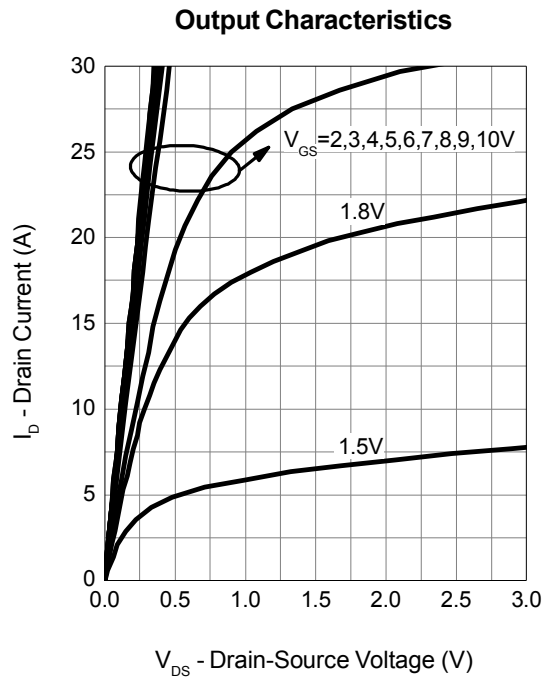
Note b Guaranteed by design, not subject to production testing.

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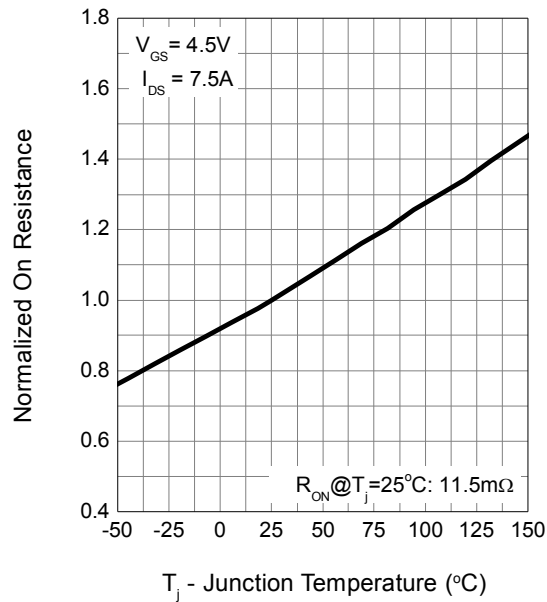
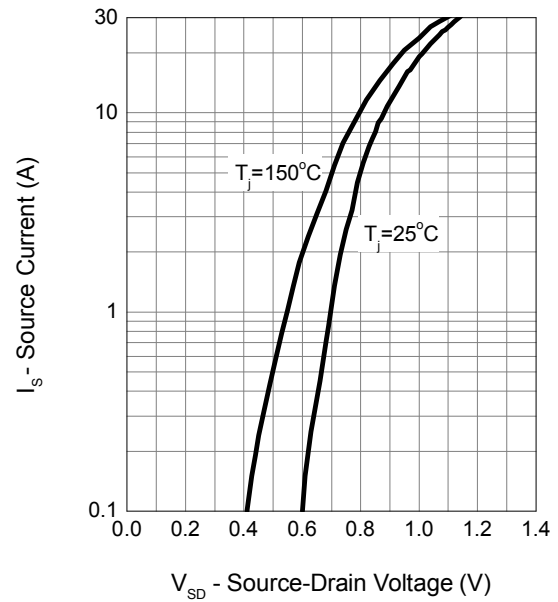
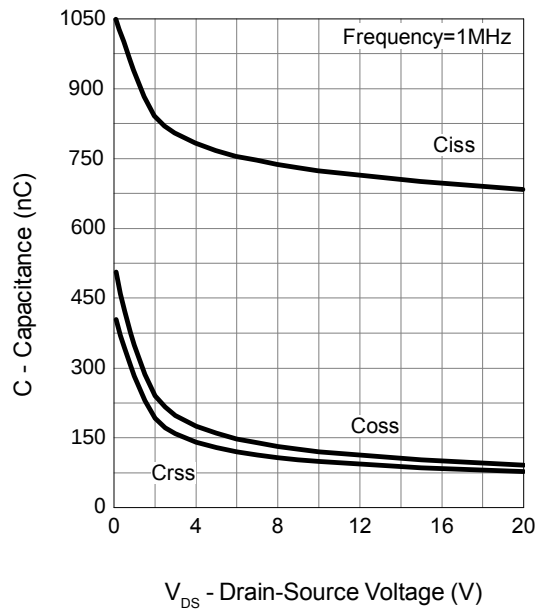
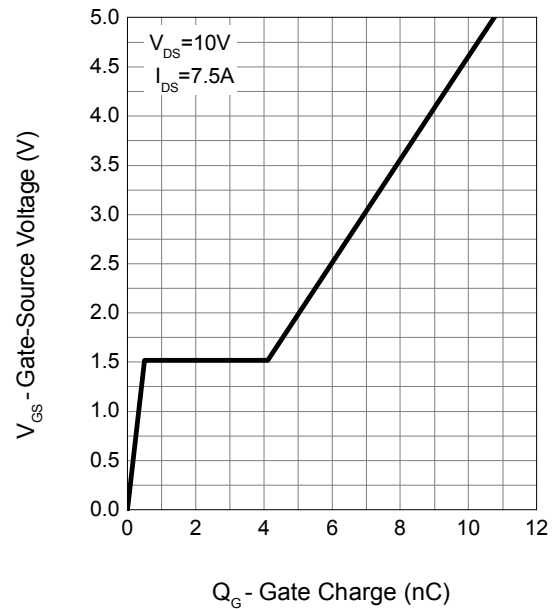
Typical Operating Characteristics



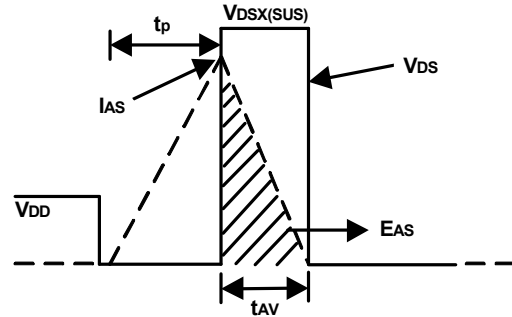
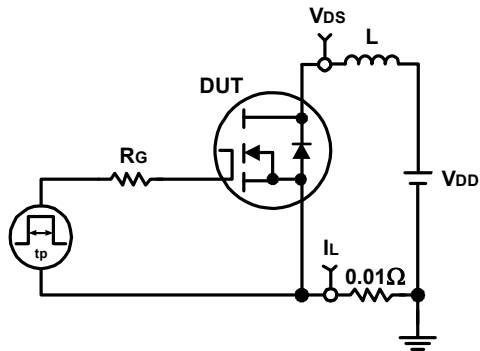
Typical Operating Characteristics (Cont.)



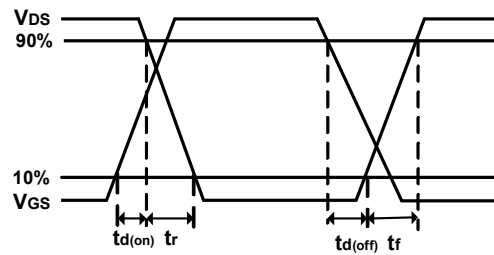
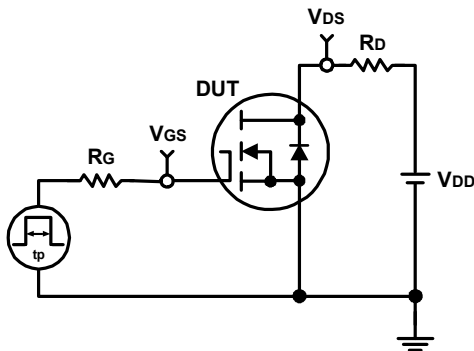
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


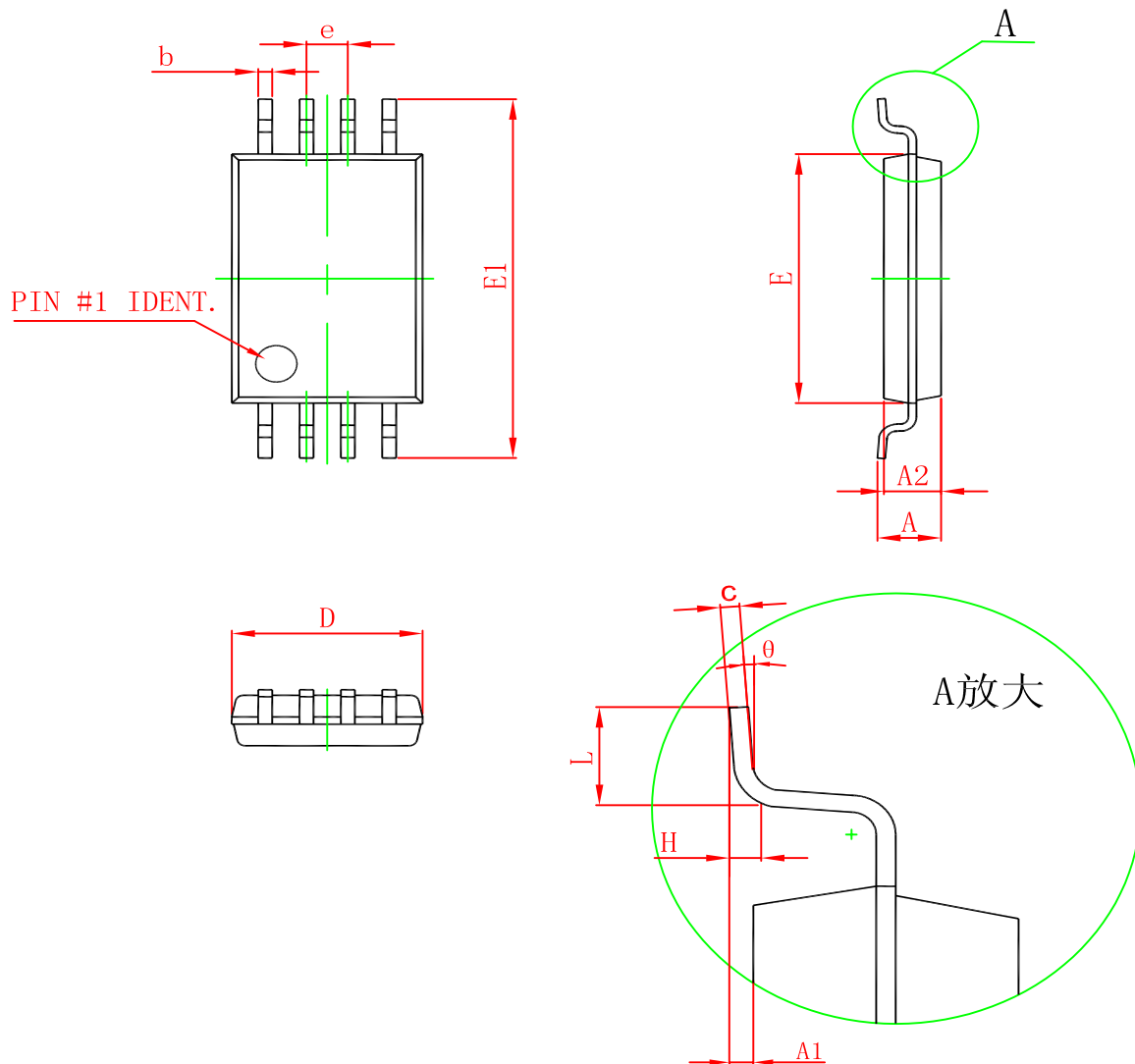
Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



■ TSSOP8 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.100		0.043
A2	0.800	1.000	0.031	0.039
A1	0.020	0.150	0.001	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028